

FEATURES

- Low noise
- Low dark current
- High response

DESCRIPTION

The **SD 060-11-41-211** is a InGaAs photodiode with high sensitivity and low noise characteristics packaged in a three leaded hermetic TO-39 metal package.

APPLICATIONS

- Communication
- Industrial
- Medical

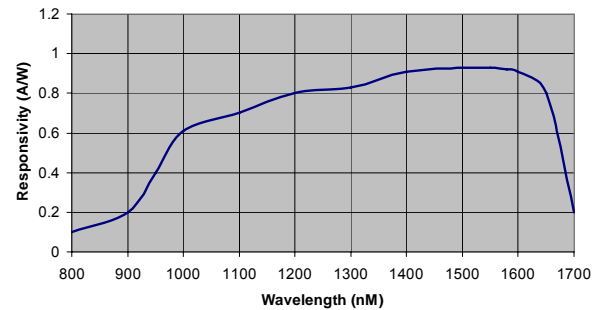


ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		75	V
T _{STG}	Storage Temperature	-55	+100	°C
T _O	Operating Temperature	-40	+85	°C
T _S	Soldering Temperature*		+260	°C

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _D	Dark Current	V _R = 5V		10	50	nA
R _{SH}	Shunt Resistance	V _R = 10 mV	2	6		MΩ
C _J	Junction Capacitance	V _R = 5V, f = 1 MHz		250	450	pF
λ range	Spectral Application Range	Spot Scan	800		1700	nm
R	Responsivity	λ = 1310nm, V _R = 5V	0.83	0.92		A/W
V _{BR}	Breakdown Voltage	I = 1μA		18		V
NEP	Noise Equivalent Power	V _R = 5V @ λ = 1310nm		1.79X10 ⁻¹⁴		W/√Hz
t _r	Response Time**	RL = 50 Ω, V _R = 5V			10	nS

**Response time of 10% to 90% is specified at 1310nm wavelength light.

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